

TECHNIQUES FOR LAYER TRANSFER PROCESSING

Abstract of the Disclosure

5 Techniques for the fabrication of semiconductor devices are provided. In one aspect, a layer transfer structure is provided. The layer transfer structure comprises a carrier substrate having a porous region with a tuned porosity in combination with an implanted species defining a separation plane therein. In another aspect, a method of forming a layer transfer structure is provided. In yet another aspect, a method of forming
10 a three dimensional integrated structure is provided.